



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#9/2
3/18/03
Jude

In re Patent Application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/932,935)
Filed: August 21, 2001)
For: LASER APPARATUS, LASER)
ANNEALING METHOD, AND)
MANUFACTURING METHOD OF A)
SEMICONDUCTOR DEVICE)

Art Unit: 2812
Examiner: V. Simkovic

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on March 4, 2003.

Adele M. Stamper
Adele M. Stamper

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

In response to the Office Action dated October 4, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please add new claims 25-45 as follows:

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--25. A method for manufacturing a semiconductor device comprising the steps of:
forming a semiconductor film on an insulating surface;
crystallizing the semiconductor film by irradiation of harmonic of a YVO₄

91 laser;

patterning the crystallized semiconductor film to form a crystallized island-like semiconductor film; and

forming at least a channel region of a thin film transistor in the crystallized island-like semiconductor film,

wherein the harmonic of the YVO₄ laser has a shape at an irradiation surface which has aspect ratio of 10 or more.

03/14/2003 NNOHAMM1 00000114 09932935

01 FC:1202
02 FC:1201

378.00 DP
588.00 DP